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| Form PTO-1449 Department of Commerce Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary) | Docket No. PAT034US | Serial No. Unassigned |
| | Applicants Anselm <i>et al.</i> | |
| | Filing Date Herewith | Group Art Unit Unassigned |

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
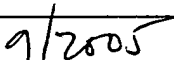
U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|--------------------|----------|-------------------------|-------|----------|-------------------------------|
| <i>Dle</i> | 4,949,350 | 08/14/99 | Jewell <i>et al.</i> | | | |
| | 5,031,187 | 07/09/91 | Orenstein <i>et al.</i> | | | |
| | 5,115,442 | 05/19/92 | Lee <i>et al.</i> | | | |
| | 5,193,098 | 03/09/93 | Welch <i>et al.</i> | | | |
| | 5,219,785 | 06/15/93 | Welch <i>et al.</i> | | | |
| <i>Dle</i> | 5,256,596 | 10/26/93 | Ackley <i>et al.</i> | | | |

FOREIGN PATENT DOCUMENTS

| | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES NO | |
|--|--------------------|------|---------|-------|----------|-------------------------|--|
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OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | | |
|---|--|-----------------|---|
|  | Qian, Y. <i>et al.</i> , "Long Wavelength (1.3 μm) Vertical-Cavity Surface-Emitting Lasers With a Wafer-Bonded Mirror and an Oxygen-Implanted Confinement Region," <i>Appl. Phys. Lett.</i> , Vol. 71, No. 1, (1997), pp. 25-27. | | |
|  | Ridgway, M. C., <i>et al.</i> , "Single-Step Implant Isolation of p^+ -InP with 5-MeV O Ions," <i>Appl. Phys. Lett.</i> , Vol. 60, No. 24, (1992), pp. 3010-3012. | | |
|  | Huffaker, D. L. <i>et al.</i> , "Native-Oxide Defined Ring Contact for Low Threshold Vertical-Cavity Lasers," <i>Appl. Phys. Lett.</i> , Vol. 65, No. 1, (1994), pp. 97-99. | | |
|  | Lee, Y. H. <i>et al.</i> , "Top-Surface-Emitting GaAs Four-Quantum-Well Lasers Emitting at $0.85\mu\text{m}$ ", <i>Electronics Letters</i> , Vol. 26, No. 11, (1990), pp.710-711. | | |
| EXAMINER |  | DATE CONSIDERED |  |

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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| U.S. PATENT DOCUMENTS | | | | | | |
| *EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
| Dle | 5,328,854 | 07/12/94 | Vakhshoori et al. | / | | |
| | 5,594,751 | 01/14/97 | Scott, Jeffrey W. | / | | |
| | 5,764,674 | 06/09/98 | Hibbs-Brenner et al. | / | | |
| | 5,893,722 | 04/13/99 | Hibbs-Brenner et al. | / | | |
| | 6,044,100 | 03/28/00 | Hobson et al. | / | | |
| Dle | 6,169,756 B1 | 01/02/01 | Chirovsky et al. | / | | |
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| FOREIGN PATENT DOCUMENTS | | | | | | |
| | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES NO |
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| | | | | | | |
| | | | | | | |
| OTHER (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | |
| Dle | Choquette, K. D., et al., "Low Threshold Voltage Vertical-Cavity Lasers Fabricated by Selective Oxidation," <i>Electronics Letters</i> , Vol. 30, No. 24, (1994), pp. 2043-2044. | | | | | |
| / | Deng, H. and Deppe, D. G., "Oxide-Confined Vertical-Cavity Lser With Additional Etched Void Confinement," <i>Electronics Letters</i> , Vol. 32, No. 10, (1996), pp. 900-901. | | | | | |
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| | | | | | | |
| EXAMINER | | | | DATE CONSIDERED | | |
| Dle | | | | 9/2005 | | |
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